

Integrated Memory Circuit and Method of Forming an Integrated Memory Circuit

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Abstract

An integrated memory circuit of the type of an NROM memory includes recessed bit lines formed of a material having a low ohmic resistance. By recessing the bit lines with
10 respect to the semiconductor substrate surface of a peripheral controlling circuit for an array of memory cells allows to form the word line lithography on a perfect or almost perfect plane so that the word line formation results in a production with higher yield and, therefore,
15 lower costs for the individual integrated memory circuit.

Fig. 8



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